

FEATURES

Complimentary to SS8550

Marking : Y1

MAXIMUM RATINGS (TA=25°C unless otherwise noted)

| Parameter | Symbol | Value | Unit |
|-------------------------------|------------------|-------------|------|
| Collector-Base Voltage | V _{CBO} | 40 | V |
| Collector-Emitter Voltage | V _{CEO} | 25 | V |
| Emitter-Base Voltage | V _{EBO} | 5 | V |
| Collector Current -Continuous | I _C | 1500 | mA |
| Collector Power Dissipation | P _C | 300 | mW |
| Junction Temperature | T _J | 150 | °C |
| Storage Temperature | T _{stg} | -55 to +150 | °C |

SS8050 (NPN)



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

| Parameter | Symbol | Test conditions | Min | Typ | Max | Unit |
|--------------------------------------|----------------------|--|-----|-----|-----|------|
| Collector-base breakdown voltage | V _{CBO} | I _C = 100μA, I _E =0 | 40 | | | V |
| Collector-emitter breakdown voltage | V _{CEO} | I _C = 0.1mA, I _B =0 | 25 | | | V |
| Emitter-base breakdown voltage | V _{EBO} | I _E =100μA, I _C =0 | 5 | | | V |
| Collector cut-off current | I _{CB} | V _{CB} =40V, I _E =0 | | | 0.1 | μA |
| Collector cut-off current | I _{CEO} | V _{CB} =20V, I _E =0 | | | 0.1 | μA |
| Emitter cut-off current | I _{EBO} | V _{EB} = 5V, I _C =0 | | | 0.1 | μA |
| DC current gain | h _{FE} (1) | V _{CE} =1V, I _C = 100mA | 120 | | 400 | |
| | h _{FE} (2) | V _{CE} =1V, I _C = 800mA | 40 | | | |
| Collector-emitter saturation voltage | V _{CE(sat)} | I _C =800mA, I _B = 80mA | | | 0.5 | V |
| Base-emitter saturation voltage | V _{BE(sat)} | I _C =800mA, I _B = 80mA | | | 1.2 | V |
| Transition frequency | f _T | V _{CE} =10V, I _C = 50mA f=30MHz | 100 | | | MHz |

CLASSIFICATION OF h_{FE}

| Rank | L | H | J |
|-------|---------|---------|---------|
| Range | 120-200 | 200-350 | 300-400 |

SS8050 Typical Characteristics

